imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



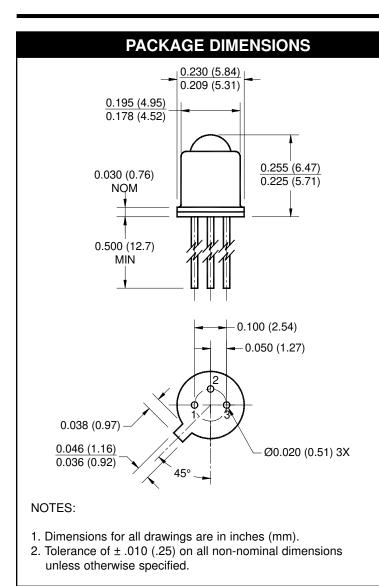
Contact us

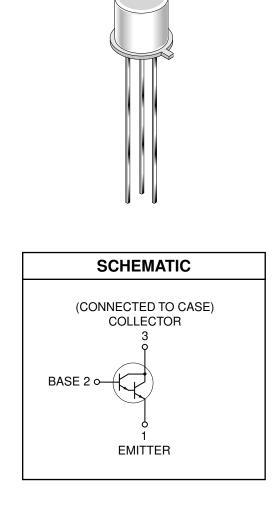
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L14F1 L14F2





DESCRIPTION

The L14F1/L14F2 are silicon photodarlingtons mounted in a narrow angle, TO-18 package.

FEATURES

- · Hermetically sealed package
- Narrow reception angle



SEMICONDUCTOR®

L14F1 L14F2

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)								
Parameter	Symbol	Rating	Unit					
Operating Temperature	T _{OPR}	-65 to +125	0°					
Storage Temperature	T _{STG}	-65 to +150	O°					
Soldering Temperature (Iron)(3,4,5 and 6)	T _{SOL-I}	240 for 5 sec	O°					
Soldering Temperature (Flow) ^(3,4 and 6)	T _{SOL-F}	260 for 10 sec	O°					
Collector to Emitter Breakdown Voltage	V _{CEO}	25	V					
Collector to Base Breakdown Voltage	V _{CBO}	25	V					
Emitter to Base Breakdwon Voltage	V _{EBO}	12	V					
Power Dissipation $(T_A = 25^{\circ}C)^{(1)}$	PD	300	mW					
Power Dissipation $(T_C = 25^{\circ}C)^{(2)}$	PD	600	mW					

NOTE:

- 1. Derate power dissipation linearly 3.00 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 6.00 mW/°C above 25°C case.

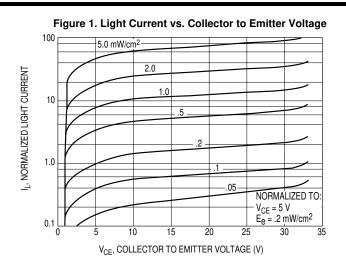
3. RMA flux is recommended.

- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension.
- 7. Light source is a GaAs LED emitting light at a peak wavelength of 940 nm.
- 8. Figure 1 and figure 2 use light source of tungsten lamp at 2870°K color temperature. A GaAs source of 0.05 mW/cm² is approximately equivalent to a tungsten source, at 2870°K, of 0.2 mW/cm².

ELECTRICAL / OPTICAL CHARACTERISTICS (T _A =25°C) (All measurements made under pulse conditions)								
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNITS		
Collector-Emitter Breakdown	$I_{\rm C} = 10 \text{ mA}, \text{ Ee} = 0$	BV _{CEO}	25		—	V		
Emitter-Base Breakdown	I _E = 100 μA, Ee = 0	BV _{EBO}	12		—	V		
Collector-Base Breakdown	$I_{\rm C} = 100 \ \mu {\rm A}, \ {\rm Ee} = 0$	BV _{CBO}	25		—	V		
Collector-Emitter Leakage	V _{CE} = 12 V, Ee = 0	I _{CEO}	—		100	nA		
Reception Angle at 1/2 Sensitivity		θ		±8		Degrees		
On-State Collector Current L14F1	$Ee = .125 \text{ mW/cm}^2, V_{CE} = 5 \text{ V}^{(7)}$	I _{C(ON)}	7.5		—	mA		
On-State Collector Current L14F2	$Ee = .125 \text{ mW/cm}^2, V_{CE} = 5 V^{(7)}$	I _{C(ON)}	2.5			mA		
Rise Time	I_{C} = 10 mA, V_{CC} = 5 V, R_{L} =100 Ω	tr		300		μs		
Fall Time	I_{C} = 10 mA, V_{CC} = 5 V, R_{L} =100 Ω	t _f		250		μs		



L14F1 L14F2



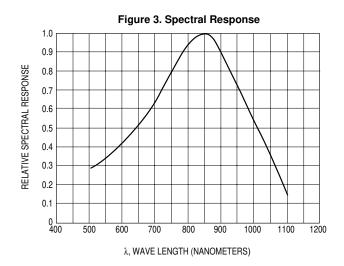
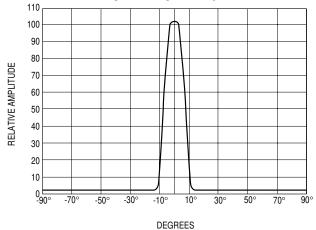


Figure 2. Relative Light Current vs. Ambient Temperature 10 IL/IL@25°C, RELATIVE LIGHT CURRENT 4 2 1.0 .8 .6 .4 .2 V_{CE} = 5 V - H = .2 mW/cm² .08 .06 .04 .02 .01 <u>–</u> -50 -25 0 25 50 75 100 125 T, TEMPERATURE (°C)

Figure 4. Angular Response



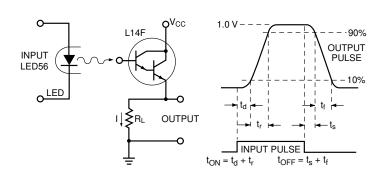
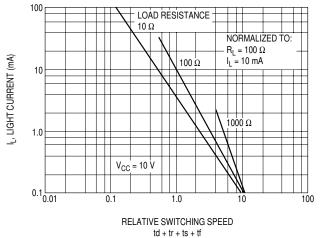


Figure 5. Test Circuit and Voltage Waveforms

Figure 6. Light Current vs. Relative Switching Speed



DS300306 6/01/01



L14F1 L14F2

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